(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
31 July 2008 (31.07.2008)

PCT

(10) International Publication Number
WO 2008/091579 A3

(51) International Patent Classification:
H01L 21/8242 (2006.01) *H01L 21/336* (2006.01)
H01L 27/108 (2006.01)

(21) International Application Number:
PCT/US2008/000785

(22) International Filing Date: 22 January 2008 (22.01.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/656,125 22 January 2007 (22.01.2007) US

(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 So. Federal Way, Boise, Idaho 83716-9632 (US).

(72) Inventor; and
(75) Inventor/Applicant *(for US only)*: **JUENGLING, Werner** [US/US]; 5660 So. Tecoma Place, Boise, Idaho 83716 (US).

(74) Agents: **CLISE, Timothy, B** et al.; Schwegman, Lundberg & Woessner, P.A., P.O. Box 2938, Minneapolis, Minnesota 55402 (US).

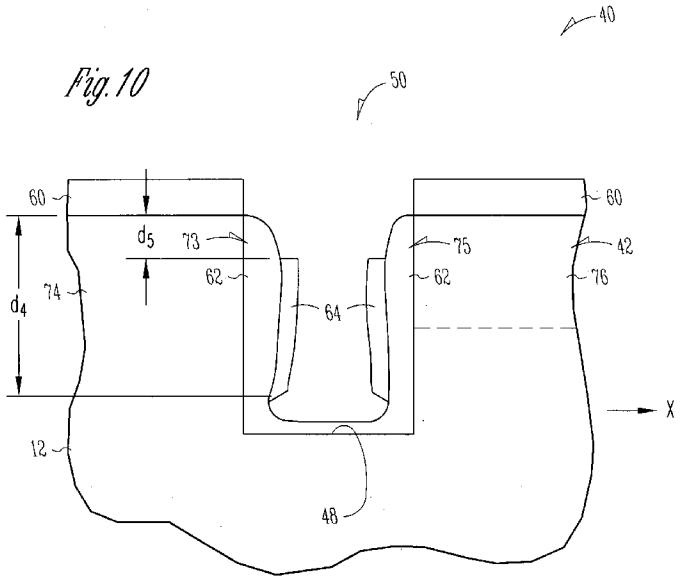
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
15 January 2009

(54) Title: MEMORY HAVING A VERTICAL ACCESS DEVICE



(57) Abstract: Semiconductor memory devices having vertical access devices are disclosed. In some embodiments, a method of forming the device includes providing a recess (50) in a semiconductor substrate (12) that includes a pair of opposed side walls (73, 75) and a floor (48) extending between the opposed side walls. A dielectric layer (62) may be deposited on the side walls and the floor of the recess. A conductive f ilm. (64) may be formed on the dielectric layer and processed to selectively remove the film from the floor of the recess and to remove at least a portion of the conductive film from the opposed sidewalls.

WO 2008/091579 A3